



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of :

Claudia Wiegand et al.

Serial No.: 10/031,787

Group Art Unit: 1763

Filed: May 20, 2002

Examiner: Olsen

For: ETCHING SOLUTION, CONTAINING HYDROFLUORIC ACID

AMENDMENT and RESPONSE

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action mailed 3 October 2002, kindly amend the above-identified application as follows.

IN THE SPECIFICATION

Please amend the specification as follows:

On page 5 delete after line 8 through line 15:

Please add the following New Paragraph on page 5 after line 15:

Brief Description of Drawings

Figure 1 depicts the mode of operation of a spin etcher.

Figure 2a depicts vertical measurement values of a wafer profile after etching with spin etch F a spin etcher.

Figure 2b depicts horizontal measurement values of a wafer profile after etching with spin etch F a spin etcher.

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